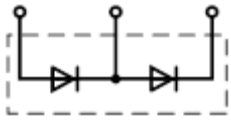


## Dual Diode Module Types

### MDD320-60N2 to MDD320-65N2

**Absolute Maximum Ratings**

$V_{RRM}$ [V]	 MDD
6000	320-60N2
6500	320-65N2

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
$V_{RRM}$	Repetitive peak reverse voltage <sup>1)</sup>	6000-6500	V
$V_{RSM}$	Non-repetitive peak reverse voltage <sup>1)</sup>	6100-6600	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{F(AV)M}$	Maximum average on-state current, $T_C = 85^\circ\text{C}$ <sup>2)</sup>	395	A
$I_{F(AV)M}$	Maximum average on-state current, $T_C = 100^\circ\text{C}$ <sup>2)</sup>	320	A
$I_{F(RMS)M}$	Nominal RMS on-state current, $T_C = 85^\circ\text{C}$ <sup>2)</sup>	625	A
$I_{F(RMS)M}$	Nominal RMS on-state current, $T_C = 100^\circ\text{C}$ <sup>2)</sup>	505	A
$I_{F(d.c.)}$	D.C. on-state current, $T_C = 55^\circ\text{C}$	715	A
$I_{FSM}$	Peak non-repetitive surge $t_p = 10$ ms, $V_{RM} = 60\%V_{RRM}$ <sup>3)</sup>	5.4	kA
$I_{FSM2}$	Peak non-repetitive surge $t_p = 10$ ms, $V_{RM} \leq 10$ V <sup>3)</sup>	6.0	kA
$I^2t$	$I^2t$ capacity for fusing $t_p = 10$ ms, $V_{RM} = 60\%V_{RRM}$ <sup>3)</sup>	146	$\text{kA}^2\text{s}$
$I^2t$	$I^2t$ capacity for fusing $t_p = 10$ ms, $V_{RM} \leq 10$ V <sup>3)</sup>	180	$\text{kA}^2\text{s}$
$V_{ISOL}$	Isolation Voltage <sup>4)</sup>	3000	V
$T_{vj\ op}$	Operating temperature range	-40 to +140	$^\circ\text{C}$
$T_{stg}$	Storage temperature range	-40 to +50	$^\circ\text{C}$

**Notes:**

- 1) De-rating factor of 0.13% per  $^\circ\text{C}$  is applicable for  $T_{vj}$  below  $25^\circ\text{C}$ .
- 2) Single phase; 50 Hz,  $180^\circ$  half-sinewave.
- 3) Half-sinewave,  $140^\circ\text{C}$   $T_{vj}$  initial.
- 4) AC RMS voltage, 50 Hz, 1min test

**Characteristics**

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS <sup>1)</sup>	UNITS
V <sub>FM</sub>	Maximum peak on-state voltage	-	-	2.40	I <sub>FM</sub> = 1570 A, T <sub>vj</sub> = 25°C	V
V <sub>F0</sub>	Threshold voltage	-	-	0.95		V
r <sub>T</sub>	Slope resistance	-	-	1.10		mΩ
I <sub>RRM</sub>	Peak reverse current	-	-	100	Rated V <sub>RRM</sub>	mA
Q <sub>rr</sub>	Recovered Charge	-	-	3600	I <sub>FM</sub> = 500 A, t <sub>p</sub> = 1 ms, di/dt = 5A/μs, V <sub>R</sub> = 100 V	μC
Q <sub>ra</sub>	Recovered Charge, 25% chord	-	-	3300		μC
I <sub>rm</sub>	Reverse recovery current	-	-	110		A
t <sub>rr</sub>	Reverse recovery time, 25% chord	-	-	60		μs
R <sub>thJC</sub>	Thermal resistance, junction to case	-	-	0.0650	Single Arm	K/W
		-	-	0.0325	Whole Module	K/W
R <sub>thCH</sub>	Thermal resistance, case to heatsink	-	-	0.020	Single Arm	K/W
		-	-	0.010	Whole Module	K/W
F <sub>1</sub>	Mounting force (to heatsink)	-	6.00	-	<sup>2)</sup>	Nm
F <sub>2</sub>	Mounting force (to terminals)	-	12.00	-		Nm
W <sub>t</sub>	Weight	-	1500	-		g

**Notes:**

- 1) Unless otherwise indicated T<sub>j</sub>=140°C.
- 2) Screws must be lubricated.

## Notes on Ratings and Characteristics

### 1.0 Voltage Grade Table

Voltage Grade	$V_{RRM}$ V	$V_{RSM}$ V	$V_R$ DC V
60	6000	6100	3600
65	6500	6600	3900

### 2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

### 3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for  $T_{vj}$  below 25°C.

### 4.0 Computer Modelling Parameters

#### 4.1 Diode Dissipation Calculations

$$I_{AV} = \frac{-V_{F0} + \sqrt{V_{F0}^2 + 4 \cdot ff^2 \cdot r_T \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_T} \quad \text{and:} \quad W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j\max} - T_C$$

Where  $V_{F0} = 0.95$  V,  $r_T = 1.10$  mΩ.

$R_{th}$  = Supplementary thermal impedance, see table below and

$ff$  = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	0.0810	0.0768	0.0742	0.0725	0.0705	0.0690	0.0650
Sine wave	0.0766	0.0724	0.0706	0.0694	0.0680		

Form Factors							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.464	2.449	2.000	1.732	1.414	1.149	1.000
Sine wave	4.025	2.778	2.220	1.879	1.568		

#### 4.2 Calculating diode $V_F$ using ABCD Coefficients

The on-state characteristic  $I_F$  vs.  $V_F$ , on page 6 is represented by a set of constants A, B, C, D, forming the coefficients of the representative equation for  $V_F$  in terms of  $I_F$  given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for  $V_F$  agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		140°C Coefficients	
A	0.97127313	A	0.9566156
B	$2.360709 \times 10^{-3}$	B	-0.0404543
C	$7.656939 \times 10^{-4}$	C	$8.818386 \times 10^{-4}$
D	$5.242400 \times 10^{-3}$	D	0.0158072

#### 4.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left( 1 - e^{\frac{-t}{\tau_p}} \right)$$

Where  $p = 1$  to  $n$  and:

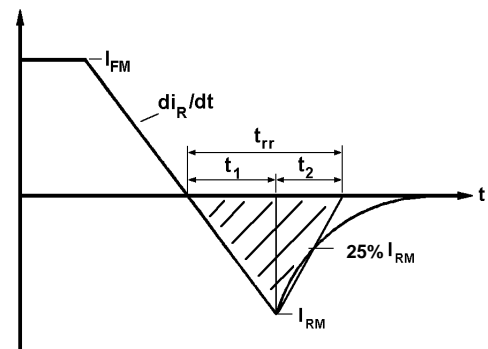
- $n$  = number of terms in the series
- $t$  = Duration of heating pulse in seconds
- $r_t$  = Thermal resistance at time  $t$
- $r_p$  = Amplitude of  $p^{\text{th}}$  term
- $\tau_p$  = Time Constant of  $r^{\text{th}}$  term

The coefficients for this device are shown in the table below:

D.C.						
Term	1	2	3	4	5	6
$r_p$	0.0385	0.01253	0.0144	0.007273	0.001871	0.0001367
$\tau_p$	3.124	0.8558	0.1999	0.009185	0.002295	0.000238

#### 5.0 Reverse recovery ratings

(i)  $Q_{rr}$  is based on 25%  $I_{RM}$  chord as shown in Fig. 1



**Fig. 1**

(ii) 
$$K \text{ Factor} = \frac{t_1}{t_2}$$

**Curves**

Figure 1 – On-state characteristics of Limit device



Figure 2 – Transient thermal impedance

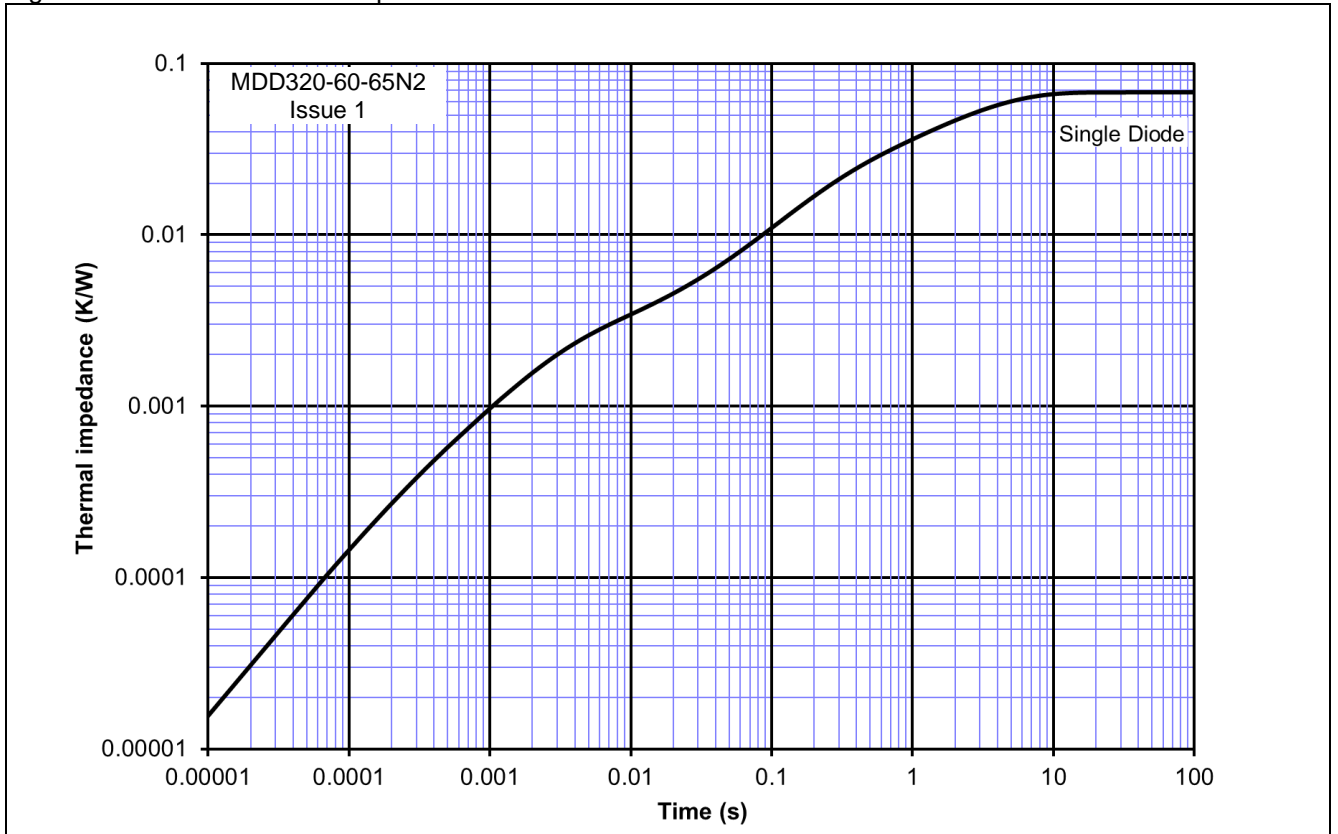


Figure 5 - Total recovered charge,  $Q_{rr}$

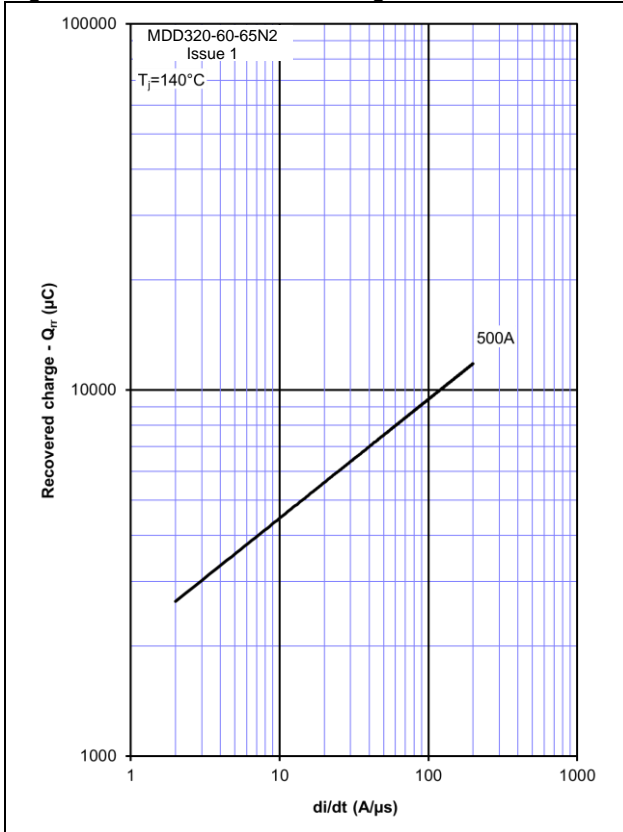


Figure 6 - Recovered charge,  $Q_{ra}$  (25% chord)

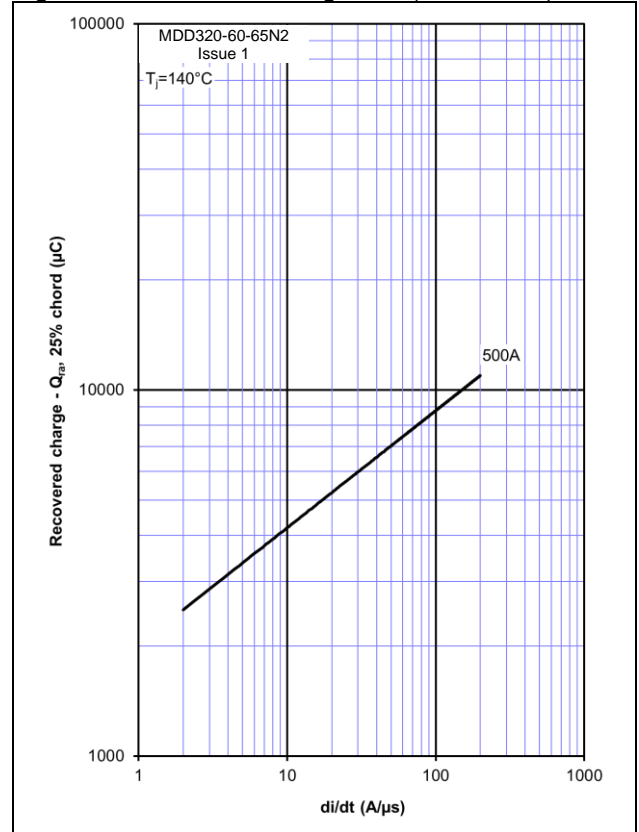


Figure 7 - Peak reverse recovery current,  $I_{rm}$

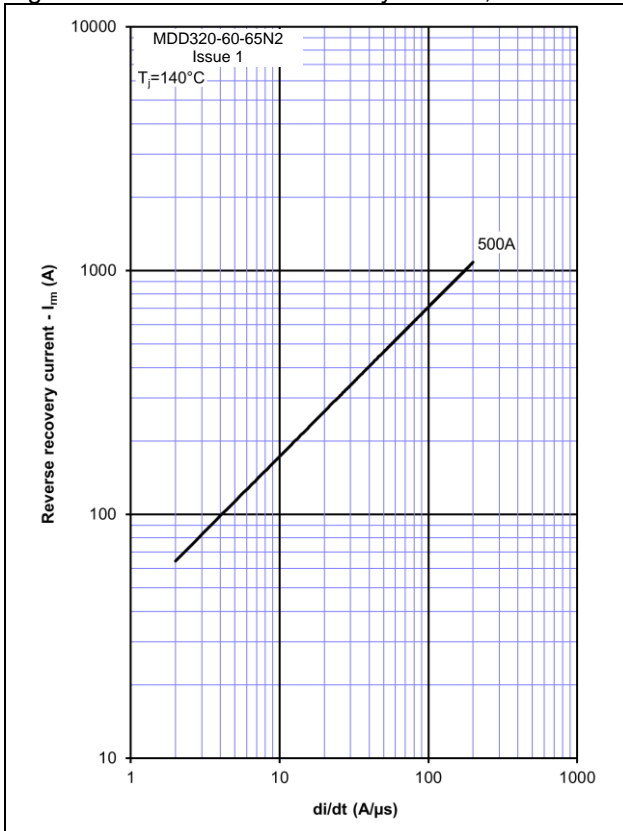


Figure 8 - Maximum recovery time,  $t_{rr}$  (25% chord)

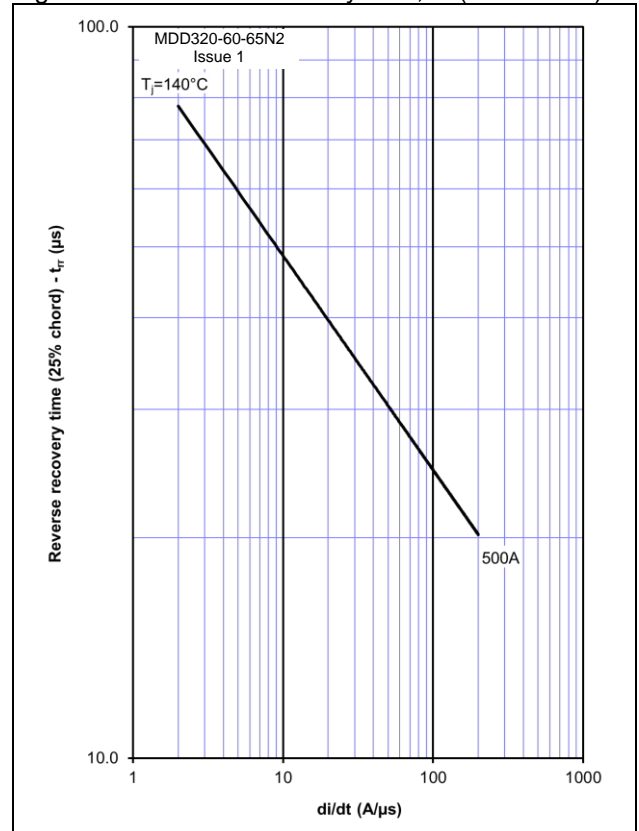


Figure 9 – On-state current vs. Power dissipation – Sine wave

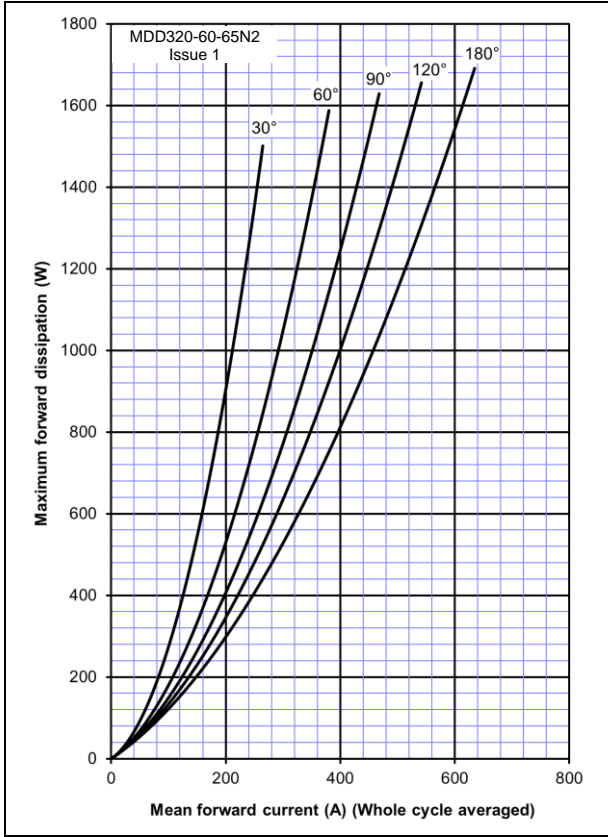


Figure 10 – On-state current vs. Heatsink temperature – Sine wave

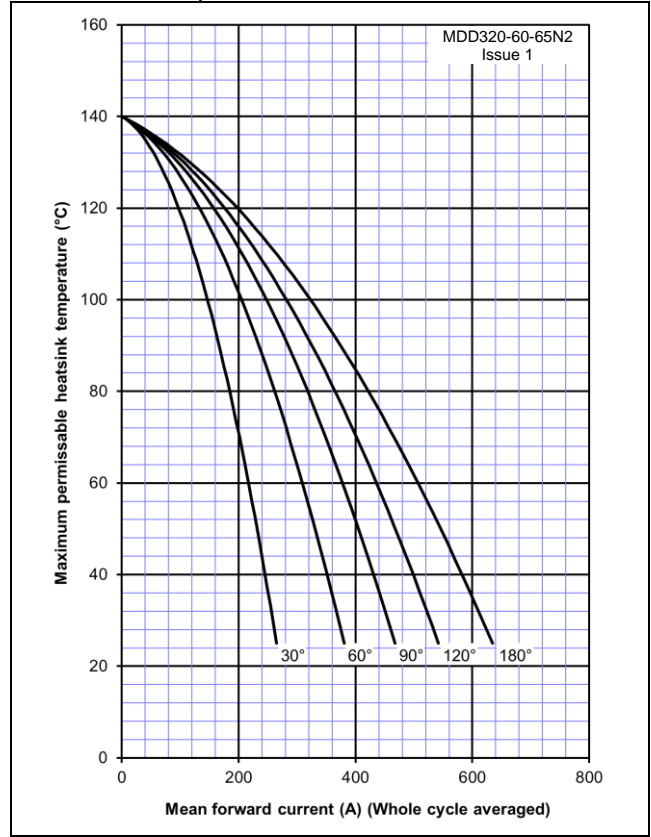


Figure 11 – On-state current vs. Power dissipation – Square wave

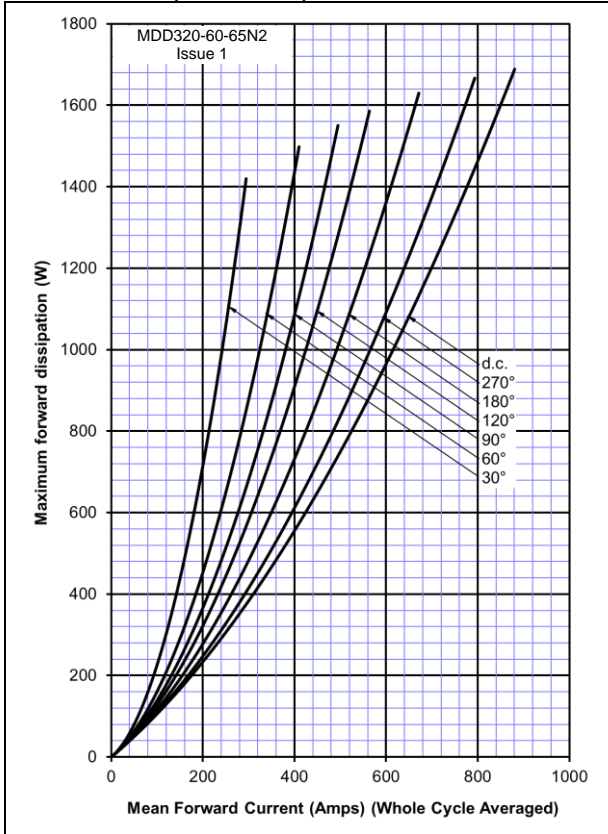


Figure 12 – On-state current vs. Heatsink temperature – Square wave

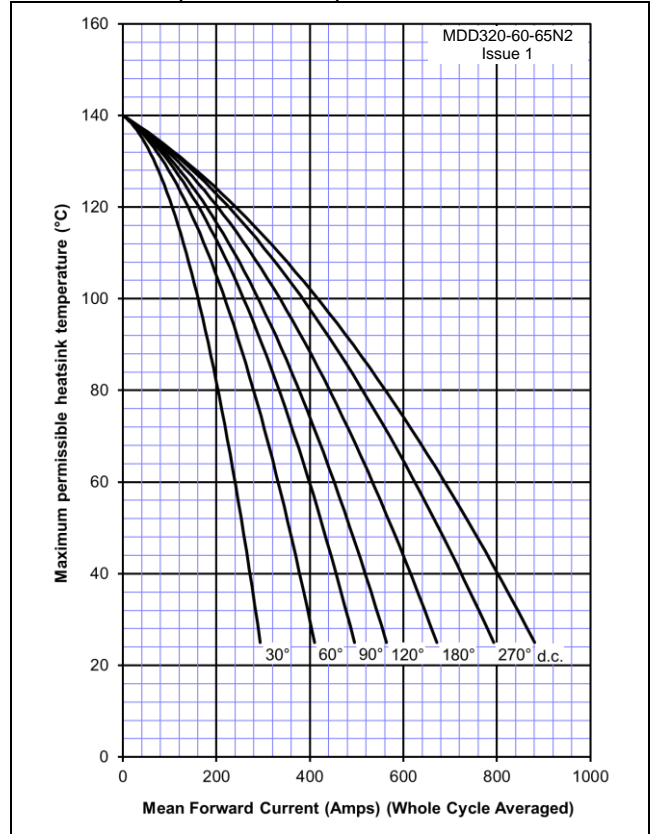
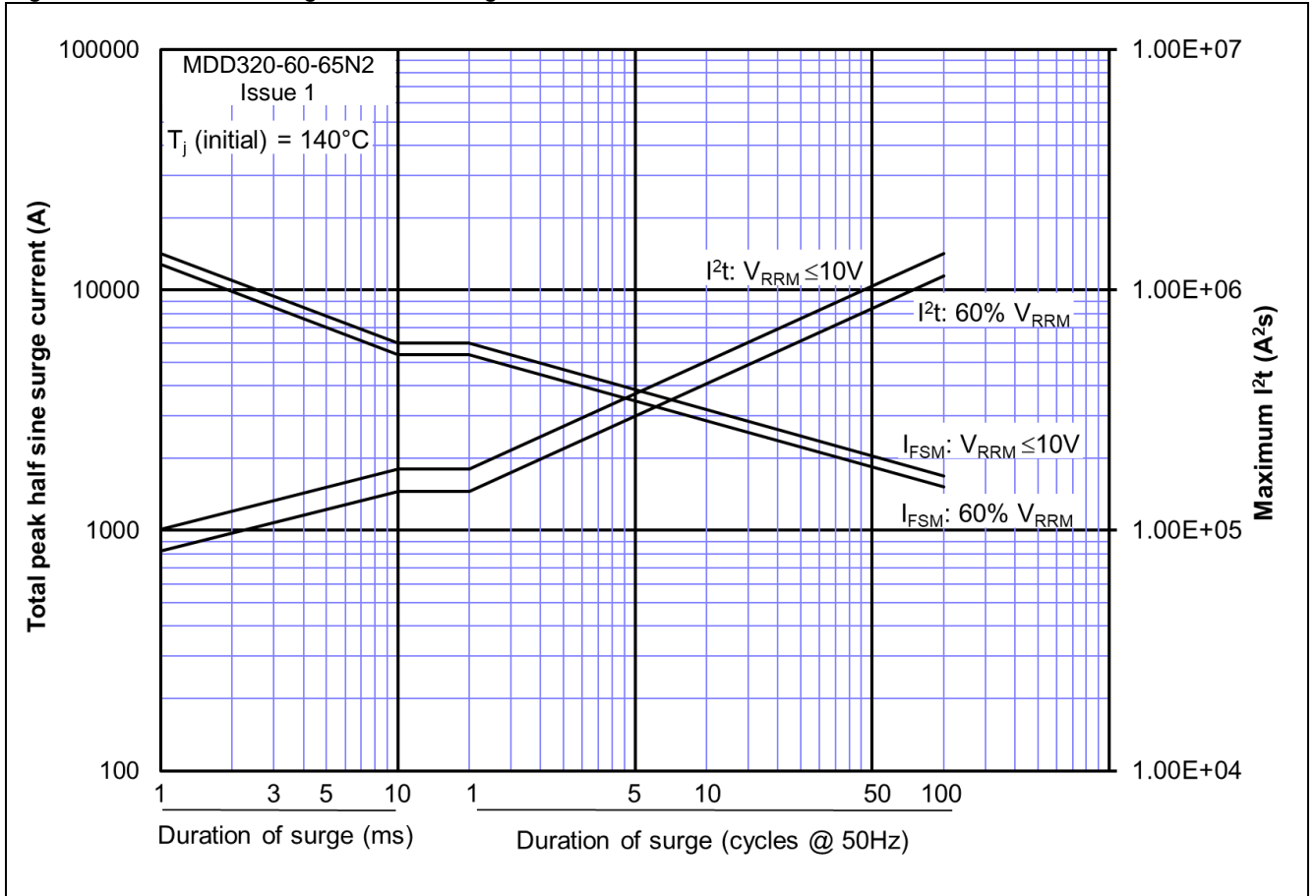
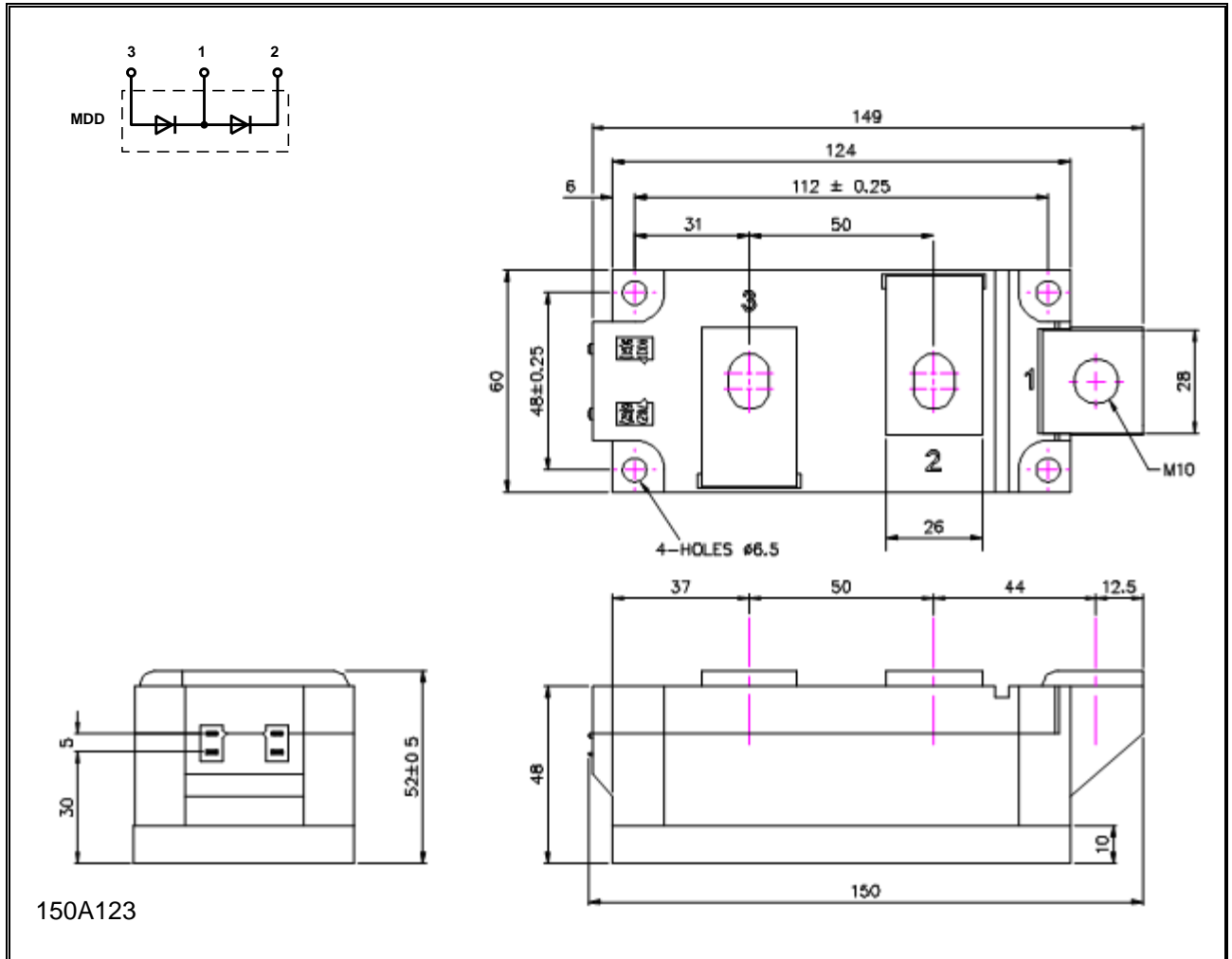




Figure 13 – Maximum surge and I<sup>2</sup>t Ratings



**Outline Drawing & Ordering Information**

**ORDERING INFORMATION**

(Please quote 11 digit code as below)

M	DD	320	◆◆	N	2
Fixed Type Code	Configuration code DD	Fixed Type Code	Voltage code $V_{RRM}/100$ 60-65	Standard Diode	Fixed Version Code

 Typical order code: MDD320-65N2– MDD configuration, 6500V  $V_{RRM}$ 

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